

DYNAMIC CHARACTERISTICS

APT34N80B2C3 LC3(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		4510		pF
C_{oss}	Output Capacitance			2050		
C_{rss}	Reverse Transfer Capacitance			110		
Q_g	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 400V$ $I_D = 34A @ 25^\circ C$		180	355	nC
Q_{gs}	Gate-Source Charge			22		
Q_{gd}	Gate-Drain ("Miller") Charge			90		
$t_{d(on)}$	Turn-on Delay Time	RESISTIVE SWITCHING $V_{GS} = 10V$ $V_{DD} = 400V$ $I_D = 34A @ 125^\circ C$ $R_G = 2.5\Omega$		25		ns
t_r	Rise Time			15		
$t_{d(off)}$	Turn-off Delay Time			70	80	
t_f	Fall Time			6	9	
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 25°C $V_{DD} = 533V, V_{GS} = 15V$ $I_D = 34A, R_G = 5\Omega$		675		μJ
E_{off}	Turn-off Switching Energy			580		
E_{on}	Turn-on Switching Energy ⑥	INDUCTIVE SWITCHING @ 125°C $V_{DD} = 533V, V_{GS} = 15V$ $I_D = 34A, R_G = 5\Omega$		1145		
E_{off}	Turn-off Switching Energy			670		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			34	Amps
I_{SM}	Pulsed Source Current ① (Body Diode)			102	
V_{SD}	Diode Forward Voltage ② ($V_{GS} = 0V, I_S = -34A$)		1	1.2	Volts
t_{rr}	Reverse Recovery Time ($I_S = -34A, di_S/dt = 100A/\mu s, V_R = 400V$)		855		ns
Q_{rr}	Reverse Recovery Charge ($I_S = -34A, di_S/dt = 100A/\mu s, V_R = 400V$)		30		μC
dv/dt	Peak Diode Recovery dv/dt ⑤			6	V/ns

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			.30	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting $T_J = +25^\circ C$, $L = 115.92mH$, $R_G = 25\Omega$, Peak $I_L = 3.4A$

⑤ $I_S = -34A$ $di/dt = 100A/\mu s$ $V_R = 480V$ $T_J = 125^\circ C$

⑥ E_{on} includes diode reverse recovery. See figures 18, 20.

⑦ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$

Microsemi reserves the right to change, without notice, the specifications and information contained herein.

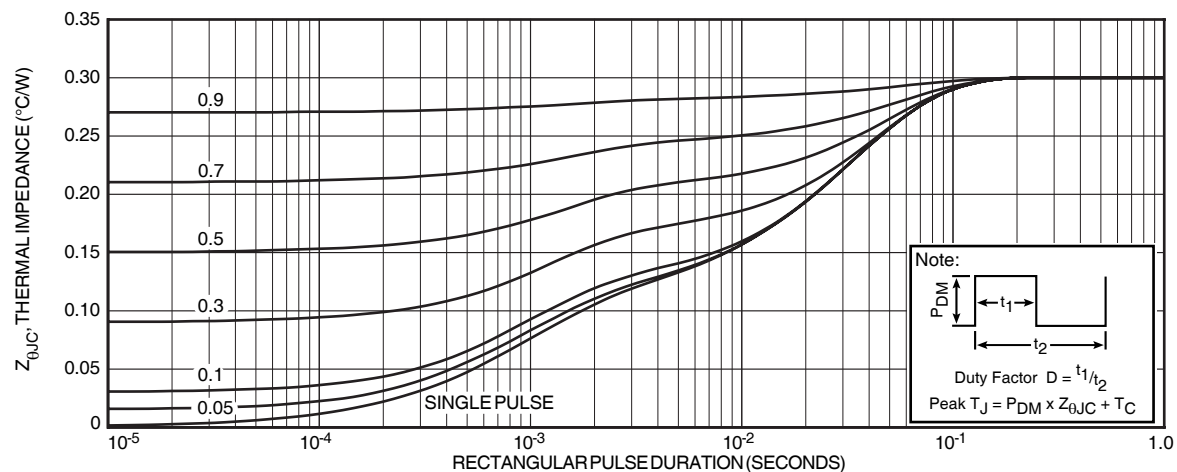


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

Typical Performance Curves

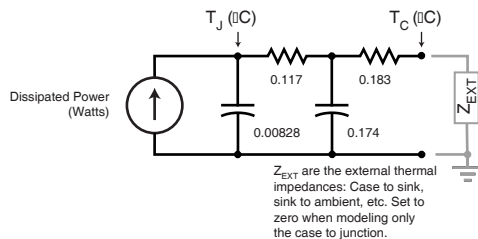


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

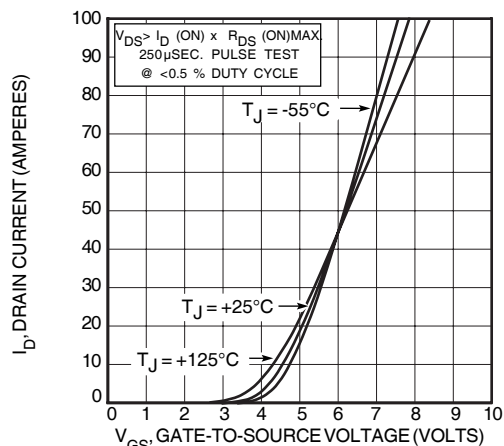


FIGURE 4, TRANSFER CHARACTERISTICS

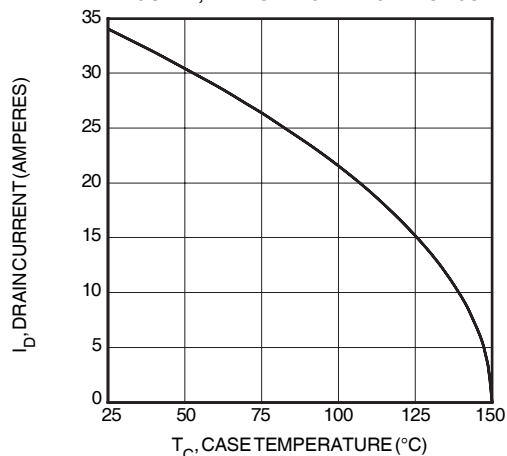


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

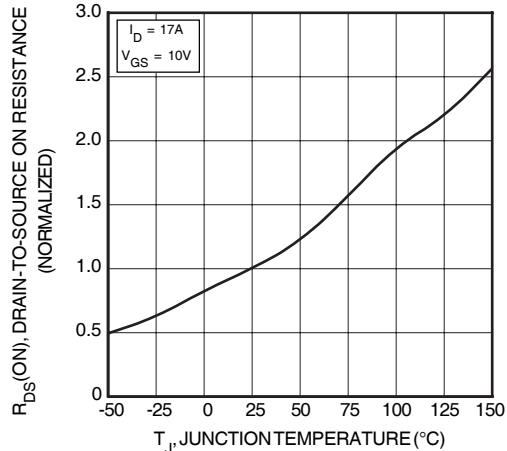


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

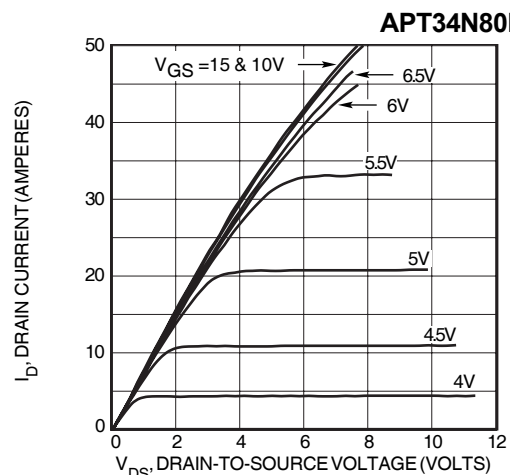


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

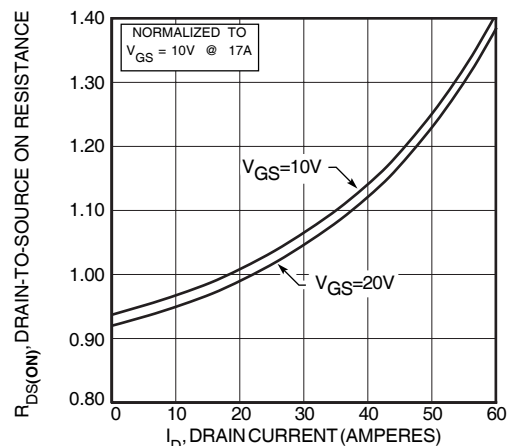


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

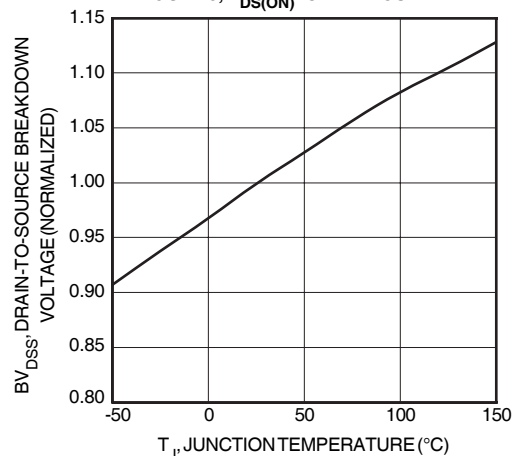


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

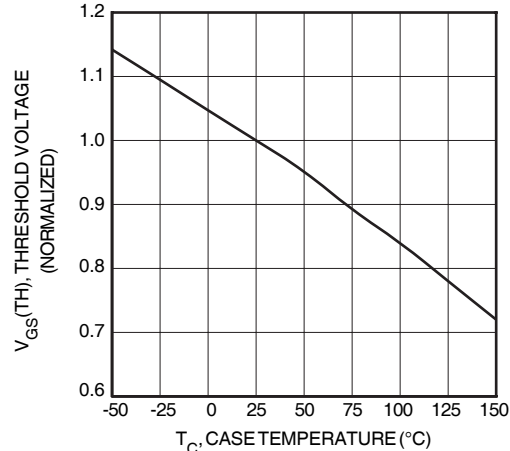


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

Typical Performance Curves

APT34N80B2C3_LC3(G)

I_D , DRAIN CURRENT (AMPERES)

Graph removed

V_{DS} , DRAIN-TO-SOURCE VOLTAGE (VOLTS)
FIGURE 10, MAXIMUM SAFE OPERATING AREA

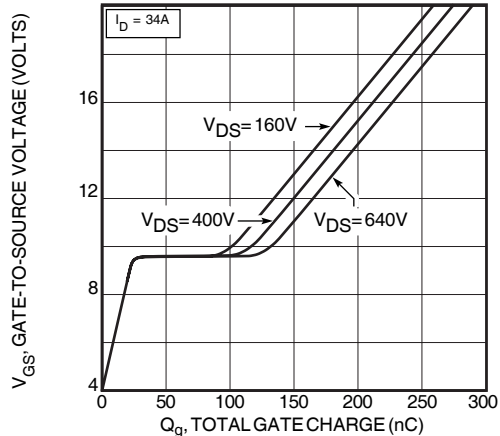


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

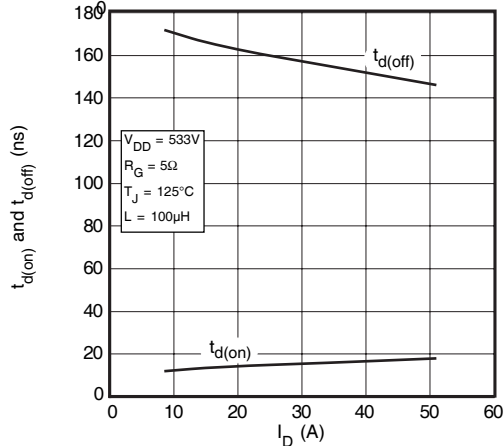


FIGURE 14, DELAY TIMES vs CURRENT

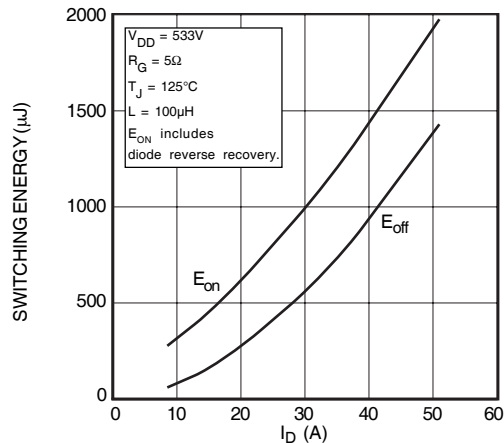


FIGURE 16, SWITCHING ENERGY vs CURRENT

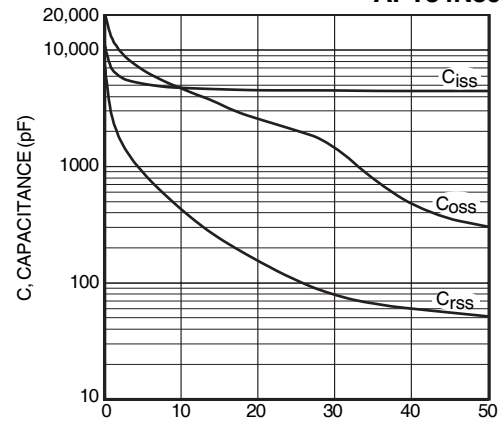


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

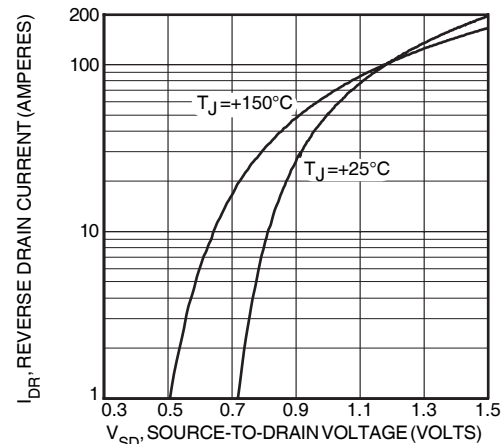


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

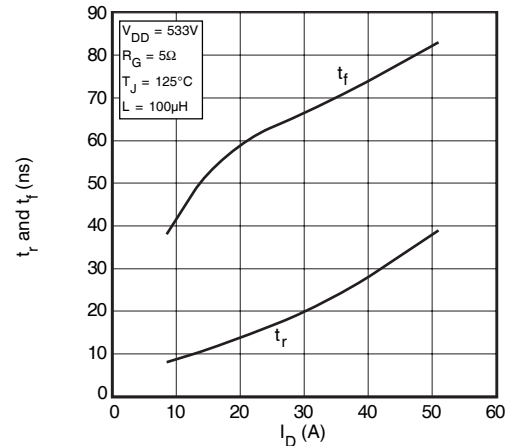


FIGURE 15, RISE AND FALL TIMES vs CURRENT

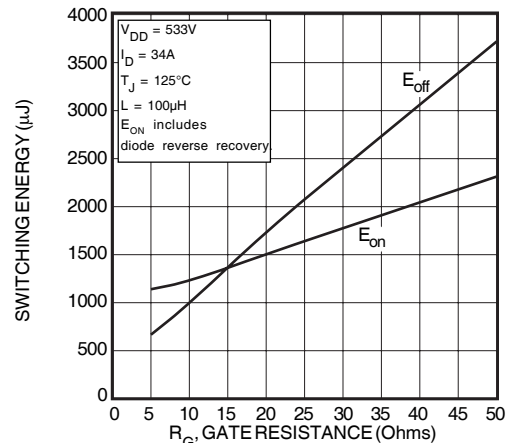


FIGURE 17, SWITCHING ENERGY VS. GATE RESISTANCE

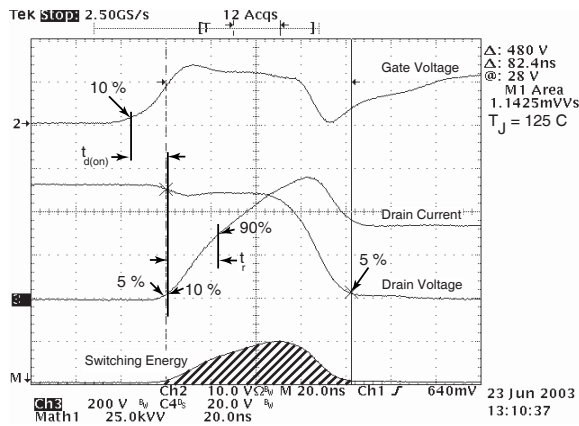


Figure 18, Turn-on Switching Waveforms and Definitions

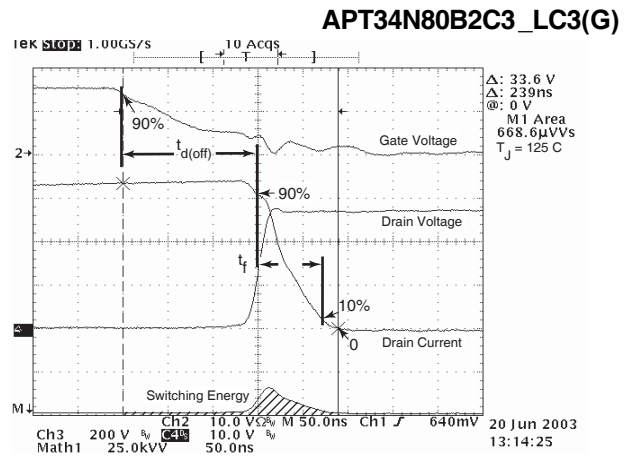


Figure 19, Turn-off Switching Waveforms and Definitions

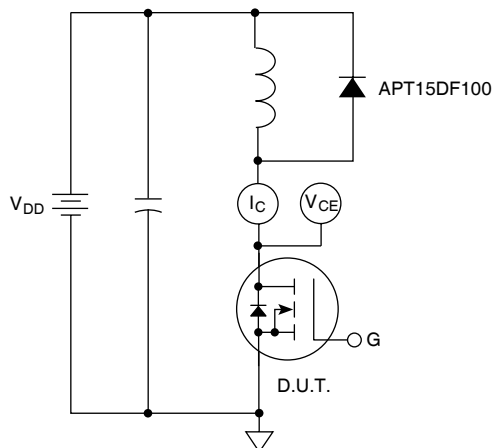
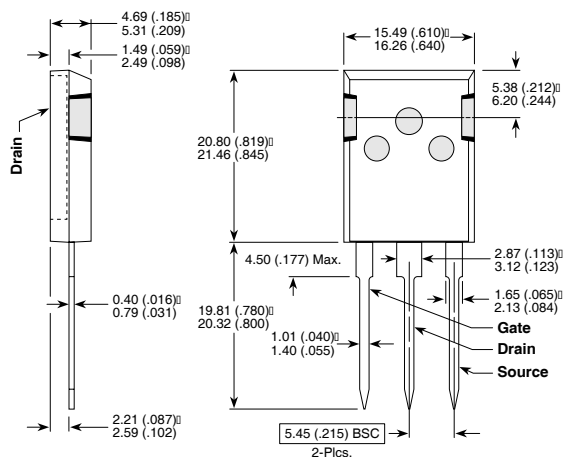


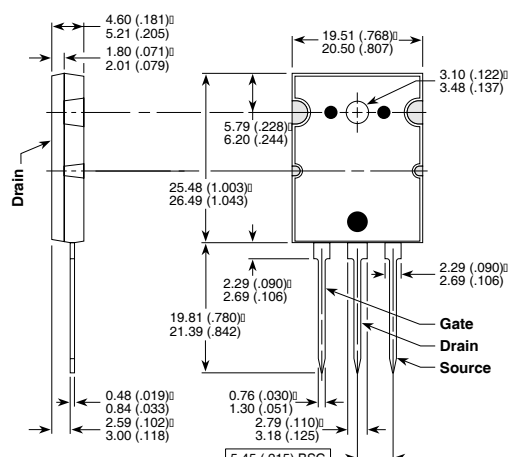
Figure 20, Inductive Switching Test Circuit

T-MAX™ (B2) Package Outline



These dimensions are equal to the TO-247 without the mounting hole.
Dimensions in Millimeters and (Inches)

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)